

L Number	Hits	Search Text	DB	Time stamp
1	1258	((dual adj damascene) or (((multilevel or multi adj level) same interconnect\$3) same semiconductor\$4)).ti,ab.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:00
2	612	(((dual adj damascene) or (((multilevel or multi adj level) same interconnect\$3) same semiconductor\$4)).ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:02
3	588	(((dual adj damascene) or (((multilevel or multi adj level) same interconnect\$3) same semiconductor\$4)).ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)) and (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:04
4	385	((((dual adj damascene) or (((multilevel or multi adj level) same interconnect\$3) same semiconductor\$4)).ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)) and (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)) and etch\$3 adj stop\$4 same (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:05
5	193	((((dual adj damascene) or (((multilevel or multi adj level) same interconnect\$3) same semiconductor\$4)).ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)) and (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)) and etch\$3 adj stop\$4 same (resist or photoresist)) and (insulat\$3 or dielectric) same ( ("USG" or oxide or "O.sub.?" ) same (high adj density adj plasma or "HDP")) or (oxide or "O.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD" or low adj pressure adj chemical adj vapor adj deposition or low adj pressure adj "CVD" or "LPCVD") or spin adj on adj glass or "SOG" or tetra adj ethyl adj ortho adj silicate or tetraethyl adj orto adj silicate or tetraethyl adj orthosilicate or tetra adj ethylorthosilicate or tetraethylorthosilicate or "TEOS" )	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:08

6	181	<p>((((((dual adj damascene) or  (((multilevel or multi adj level) same  interconnect\$3) same  semiconduct\$4)).ti,ab.) and etch\$3 adj  stop\$4 same (insulat\$3 or dielectric\$4))  and (via or hole or void or opening or  trench\$3 or plug\$3) same (conduct\$4 or  metal\$8)) and etch\$3 adj stop\$4 same  (resist or photoresist)) and (insulat\$3 or  dielectric) same ( ("USG" or oxide or  "O.sub.?" ) same (high adj density adj  plasma or "HDP")) or (oxide or "O.sub.?" )  same (plasma adj enhanced adj chemical adj  vapor adj deposition or plasma adj  enhanced adj "CVD" or plasma adj "ECVD" or  "PECVD" or low adj pressure adj chemical  adj vapor adj deposition or low adj  pressure adj "CVD" or "LPCVD") or spin adj  on adj glass or "SOG" or tetra adj ethyl  adj ortho adj silicate or tetraethyl adj  orto adj silicate or tetraethyl adj  orthosilicate or tetra adj  ethylorthosilicate or  tetraethylorthosilicate or "TEOS" )) and  (insulat\$3 or dielectric) same thick\$4</p>	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:09
7	90	<p>((((((dual adj damascene) or  (((multilevel or multi adj level) same  interconnect\$3) same  semiconduct\$4)).ti,ab.) and etch\$3 adj  stop\$4 same (insulat\$3 or dielectric\$4))  and (via or hole or void or opening or  trench\$3 or plug\$3) same (conduct\$4 or  metal\$8)) and etch\$3 adj stop\$4 same  (resist or photoresist)) and (insulat\$3 or  dielectric) same ( ("USG" or oxide or  "O.sub.?" ) same (high adj density adj  plasma or "HDP")) or (oxide or "O.sub.?" )  same (plasma adj enhanced adj chemical adj  vapor adj deposition or plasma adj  enhanced adj "CVD" or plasma adj "ECVD" or  "PECVD" or low adj pressure adj chemical  adj vapor adj deposition or low adj  pressure adj "CVD" or "LPCVD") or spin adj  on adj glass or "SOG" or tetra adj ethyl  adj ortho adj silicate or tetraethyl adj  orto adj silicate or tetraethyl adj  orthosilicate or tetra adj  ethylorthosilicate or  tetraethylorthosilicate or "TEOS" )) and  (insulat\$3 or dielectric) same thick\$4  and etch\$3 adj stop\$4 same ( (nitride or  "N.sub.?" ) same (plasma adj enhanced adj  chemical adj vapor adj deposition or  plasma adj enhanced adj "CVD" or plasma  adj "ECVD" or "PECVD")) or (silicon or  "Si") adj oxynitride or siliconoxynitride  or silicon adj "ON" or "SiON" or (tantalum  or "Ta") adj oxide or "Ta.sub.2" adj  "O.sub.5" or (zinc or "Zn") adj oxide or  "Zn" adj "O.sub.2" or "ZnO" or (zirconium  or "Zr") adj oxide or "Zr" adj "O.sub.2"  or (hafnium or "Hf") adj oxide or "HfO" or  (aluminum or "Al") adj oxide or "Al.sub.2"  adj "O.sub.3" )</p>	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:11

8	83	((((((((dual adj damascene) or (((multilevel or multi adj level) same interconnect\$3) same semiconduct\$4)).ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)) and (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)) and etch\$3 adj stop\$4 same (resist or photoresist)) and (insulat\$3 or dielectric) same ( ("USG" or oxide or "O.sub.?" ) same (high adj density adj plasma or "HDP")) or (oxide or "O.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD" or low adj pressure adj chemical adj vapor adj deposition or low adj pressure adj "CVD" or "LPCVD") or spin adj on adj glass or "SOG" or tetra adj ethyl adj ortho adj silicate or tetraethyl adj orto adj silicate or tetraethyl adj orthosilicate or tetra adj ethylorthosilicate or tetraethylorthosilicate or "TEOS" )) and (insulat\$3 or dielectric) same thick\$4) and etch\$3 adj stop\$4 same ( ((nitride or "N.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD")) or (silicon or "Si") adj oxynitride or siliconoxynitride or silicon adj "ON" or "SiON" or (tantalum or "Ta") adj oxide or "Ta.sub.2" adj "O.sub.5" or (zinc or "Zn") adj oxide or "Zn" adj "O.sub."2 or "ZnO" or (zirconium or "Zr") adj oxide or "Zr" adj "O.sub.2" or (hafnium or "Hf") adj oxide or "HfO" or (aluminum or "Al") adj oxide or "Al.sub.2" adj "O.sub.3" )) and etch\$3 adj stop\$4 same thick\$4	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:12
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9	80	((((((((dual adj damascene) or (((multilevel or multi adj level) same interconnect\$3) same semiconduct\$4)).ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)) and (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)) and etch\$3 adj stop\$4 same (resist or photoresist)) and (insulat\$3 or dielectric) same ( ("USG" or oxide or "O.sub.?" ) same (high adj density adj plasma or "HDP")) or (oxide or "O.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD" or low adj pressure adj chemical adj vapor adj deposition or low adj pressure adj "CVD" or "LPCVD") or spin adj on adj glass or "SOG" or tetra adj ethyl adj ortho adj silicate or tetraethyl adj orto adj silicate or tetraethyl adj orthosilicate or tetra adj ethylorthosilicate or tetraethylorthosilicate or "TEOS" )) and (insulat\$3 or dielectric) same thick\$4) and etch\$3 adj stop\$4 same ( ((nitride or "N.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD")) or (silicon or "Si") adj oxynitride or siliconoxynitride or silicon adj "ON" or "SiON" or (tantalum or "Ta") adj oxide or "Ta.sub.2" adj "O.sub.5" or (zinc or "Zn") adj oxide or "Zn" adj "O.sub.2" or "ZnO" or (zirconium or "Zr") adj oxide or "Zr" adj "O.sub.2" or (hafnium or "Hf") adj oxide or "HfO" or (aluminum or "Al") adj oxide or "Al.sub.2" adj "O.sub.3" )) and etch\$3 adj stop\$4 same thick\$4) and (conduct\$4 or metal\$8) same (aluminum or "Al" or copper or "Cu" or gold or "Au" or silver or "Ag" or chrome or chromium or "Cr")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:14
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10	64	<p>(((((dual adj damascene) or ((multilevel or multi adj level) same interconnect\$3) same semiconductor\$.ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)) and (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)) and etch\$3 adj stop\$4 same (resist or photoresist)) and (insulat\$3 or dielectric) same ( ("USG" or oxide or "O.sub.?" ) same (high adj density adj plasma or "HDP")) or (oxide or "O.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD" or low adj pressure adj chemical adj vapor adj deposition or low adj pressure adj "CVD" or "LPCVD") or spin adj on adj glass or "SOG" or tetra adj ethyl adj ortho adj silicate or tetraethyl adj orto adj silicate or tetraethyl adj orthosilicate or tetra adj ethylorthosilicate or tetraethylorthosilicate or "TEOS" )) and (insulat\$3 or dielectric) same thick\$4) and etch\$3 adj stop\$4 same ( (nitride or "N.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD")) or (silicon or "Si") adj oxynitride or siliconoxynitride or silicon adj "ON" or "SiON" or (tantalum or "Ta") adj oxide or "Ta.sub.2" adj "O.sub.5" or (zinc or "Zn") adj oxide or "Zn" adj "O.sub.2" or "ZnO" or (zirconium or "Zr") adj oxide or "Zr" adj "O.sub.2" or (hafnium or "Hf") adj oxide or "HfO" or (aluminum or "Al") adj oxide or "Al.sub.2" adj "O.sub.3" )) and etch\$3 adj stop\$4 same thick\$4) and (conduct\$4 or metal\$8) same (aluminum or "Al" or copper or "Cu" or gold or "Au" or silver or "Ag" or chrome or chromium or "Cr")) and (conduct\$4 or metal\$8 or aluminum or "Al" or copper or "Cu" or gold or "Au" or silver or "Ag" or chrome or chromium or "Cr") same thick\$4</p>	<p>USPAT; US-PGPUB; EPO; JPO; IBM_TDB</p>	2004/02/19 08:17
11	2819	430/312,314,316-317.ccls.	<p>USPAT; US-PGPUB; EPO; JPO; IBM_TDB</p>	2004/02/19 08:20
12	8322	438/584,622,624,637-638,700,702,723-724.ccls	<p>USPAT; US-PGPUB; EPO; JPO; IBM_TDB</p>	2004/02/19 08:20
13	2261	dual adj damascene and (etch\$3 near3 stop\$4 or hardmask\$3 or hard\$4 near3 mask\$3)	<p>USPAT; US-PGPUB; EPO; JPO; IBM_TDB</p>	2004/02/19 08:22



-	550	((((dual adj damascene) or (((multilevel or multi adj level) same interconnect\$3) same semiconductor\$4)).ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:01
-	527	((((dual adj damascene) or (((multilevel or multi adj level) same interconnect\$3) same semiconductor\$4)).ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)) and (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:03
-	346	(((((dual adj damascene) or (((multilevel or multi adj level) same interconnect\$3) same semiconductor\$4)).ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)) and (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)) and etch\$3 adj stop\$4 same (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:04
-	179	(((((dual adj damascene) or (((multilevel or multi adj level) same interconnect\$3) same semiconductor\$4)).ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)) and (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)) and etch\$3 adj stop\$4 same (resist or photoresist)) and (insulat\$3 or dielectric) same ( ("USG" or oxide or "O.sub.?" ) same (high adj density adj plasma or "HDP")) or (oxide or "O.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD" or low adj pressure adj chemical adj vapor adj deposition or low adj pressure adj "CVD" or "LPCVD" ) or spin adj on adj glass or "SOG" or tetra adj ethyl adj ortho adj silicate or tetraethyl adj orto adj silicate or tetraethyl adj orthosilicate or tetra adj ethylorthosilicate or tetraethylorthosilicate or "TEOS" )	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:05
-	168	((((((dual adj damascene) or (((multilevel or multi adj level) same interconnect\$3) same semiconductor\$4)).ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)) and (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)) and etch\$3 adj stop\$4 same (resist or photoresist)) and (insulat\$3 or dielectric) same ( ("USG" or oxide or "O.sub.?" ) same (high adj density adj plasma or "HDP")) or (oxide or "O.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD" or low adj pressure adj chemical adj vapor adj deposition or low adj pressure adj "CVD" or "LPCVD" ) or spin adj on adj glass or "SOG" or tetra adj ethyl adj ortho adj silicate or tetraethyl adj orto adj silicate or tetraethyl adj orthosilicate or tetra adj ethylorthosilicate or tetraethylorthosilicate or "TEOS" )) and (insulat\$3 or dielectric) same thick\$4	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:08

-	84	(((((((dual adj damascene) or (((multilevel or multi adj level) same interconnect\$3) same semiconduct\$4)).ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)) and (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)) and etch\$3 adj stop\$4 same (resist or photoresist)) and (insulat\$3 or dielectric) same ( ("USG" or oxide or "O.sub."?) same (high adj density adj plasma or "HDP")) or (oxide or "O.sub."?) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD" or low adj pressure adj chemical adj vapor adj deposition or low adj pressure adj "CVD" or "LPCVD") or spin adj on adj glass or "SOG" or tetra adj ethyl adj ortho adj silicate or tetraethyl adj orto adj silicate or tetraethyl adj orthosilicate or tetra adj ethylorthosilicate or tetraethylorthosilicate or "TEOS" )) and (insulat\$3 or dielectric) same thick\$4) and etch\$3 adj stop\$4 same ( ((nitride or "N.sub."?) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD")) or (silicon or "Si") adj oxynitride or siliconoxynitride or silicon adj "ON" or "SiON" or (tantalum or "Ta") adj oxide or "Ta.sub.2" adj "O.sub.5" or (zinc or "Zn") adj oxide or "Zn" adj "O.sub."2 or "ZnO" or (zirconium or "Zr") adj oxide or "Zr" adj "O.sub.2" or (hafnium or "Hf") adj oxide or "HfO" or (aluminum or "Al") adj oxide or "Al.sub.2" adj "O.sub.3" )	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:09
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-	77	((((((((dual adj damascene) or (((multilevel or multi adj level) same interconnect\$3) same semiconduct\$4)).ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)) and (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)) and etch\$3 adj stop\$4 same (resist or photoresist)) and (insulat\$3 or dielectric) same ( ("USG" or oxide or "O.sub.?" ) same (high adj density adj plasma or "HDP")) or (oxide or "O.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD" or low adj pressure adj chemical adj vapor adj deposition or low adj pressure adj "CVD" or "LPCVD") or spin adj on adj glass or "SOG" or tetra adj ethyl adj ortho adj silicate or tetraethyl adj orto adj silicate or tetraethyl adj orthosilicate or tetra adj ethylorthosilicate or tetraethylorthosilicate or "TEOS" )) and (insulat\$3 or dielectric) same thick\$4) and etch\$3 adj stop\$4 same ( ((nitride or "N.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD")) or (silicon or "Si") adj oxynitride or siliconoxynitride or silicon adj "ON" or "SiON" or (tantalum or "Ta") adj oxide or "Ta.sub.2" adj "O.sub.5" or (zinc or "Zn") adj oxide or "Zn" adj "O.sub."2 or "ZnO" or (zirconium or "Zr") adj oxide or "Zr" adj "O.sub.2" or (hafnium or "Hf") adj oxide or "HfO" or (aluminum or "Al") adj oxide or "Al.sub.2" adj "O.sub.3" )) and etch\$3 adj stop\$4 same thick\$4	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:12
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-	75	((((((((dual adj damascene) or (((multilevel or multi adj level) same interconnect\$3) same semiconduct\$4)).ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)) and (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)) and etch\$3 adj stop\$4 same (resist or photoresist)) and (insulat\$3 or dielectric) same ( ("USG" or oxide or "O.sub.?" ) same (high adj density adj plasma or "HDP")) or (oxide or "O.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD" or low adj pressure adj chemical adj vapor adj deposition or low adj pressure adj "CVD" or "LPCVD") or spin adj on adj glass or "SOG" or tetra adj ethyl adj ortho adj silicate or tetraethyl adj ortho adj silicate or tetraethyl adj orthosilicate or tetra adj ethylorthosilicate or tetraethylorthosilicate or "TEOS" )) and (insulat\$3 or dielectric) same thick\$4) and etch\$3 adj stop\$4 same ( (nitride or "N.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD")) or (silicon or "Si") adj oxynitride or siliconoxynitride or silicon adj "ON" or "SiON" or (tantalum or "Ta") adj oxide or "Ta.sub.2" adj "O.sub.5" or (zinc or "Zn") adj oxide or "Zn" adj "O.sub.2" or "ZnO" or (zirconium or "Zr") adj oxide or "Zr" adj "O.sub.2" or (hafnium or "Hf") adj oxide or "HfO" or (aluminum or "Al") adj oxide or "Al.sub.2" adj "O.sub.3" )) and etch\$3 adj stop\$4 same thick\$4) and (conduct\$4 or metal\$8) same (aluminum or "Al" or copper or "Cu" or gold or "Au" or silver or "Ag" or chrome or chromium or "Cr")	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:14
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-	59	((((((((((dual adj damascene) or (((multilevel or multi adj level) same interconnect\$3) same semiconduct\$4)).ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)) and (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)) and etch\$3 adj stop\$4 same (resist or photoresist)) and (insulat\$3 or dielectric) same ( ("USG" or oxide or "O.sub.?" ) same (high adj density adj plasma or "HDP")) or (oxide or "O.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD" or low adj pressure adj chemical adj vapor adj deposition or low adj pressure adj "CVD" or "LPCVD") or spin adj on adj glass or "SOG" or tetra adj ethyl adj ortho adj silicate or tetraethyl adj orto adj silicate or tetraethyl adj orthosilicate or tetra adj ethylorthosilicate or tetraethylorthosilicate or "TEOS" )) and (insulat\$3 or dielectric) same thick\$4) and etch\$3 adj stop\$4 same ( ((nitride or "N.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD")) or (silicon or "Si") adj oxynitride or siliconoxynitride or silicon adj "ON" or "SiON" or (tantalum or "Ta") adj oxide or "Ta.sub.2" adj "O.sub.5" or (zinc or "Zn") adj oxide or "Zn" adj "O.sub.2" or "ZnO" or (zirconium or "Zr") adj oxide or "Zr" adj "O.sub.2" or (hafnium or "Hf") adj oxide or "HfO" or (aluminum or "Al") adj oxide or "Al.sub.2" adj "O.sub.3" )) and etch\$3 adj stop\$4 same thick\$4) and (conduct\$4 or metal\$8) same (aluminum or "Al" or copper or "Cu" or gold or "Au" or silver or "Ag" or chrome or chromium or "Cr")) and (conduct\$4 or metal\$8 or aluminum or "Al" or copper or "Cu" or gold or "Au" or silver or "Ag" or chrome or chromium or "Cr") same thick\$4	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:17
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-	681	((430/312,314,316-317.ccls. or 438/584,622,624,637-638,700,702,723-724.ccls and (dual adj damascene and (etch\$3 near3 stop\$4 or hardmask\$3 or hard\$4 near3 mask\$3))) not ((((((((((dual adj damascene) or ((multilevel or multi adj level) same interconnect\$3) same semiconduct\$4)).ti,ab.) and etch\$3 adj stop\$4 same (insulat\$3 or dielectric\$4)) and (via or hole or void or opening or trench\$3 or plug\$3) same (conduct\$4 or metal\$8)) and etch\$3 adj stop\$4 same (resist or photoresist)) and (insulat\$3 or dielectric) same ( ("USG" or oxide or "O.sub.?" ) same (high adj density adj plasma or "HDP")) or (oxide or "O.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD" or low adj pressure adj chemical adj vapor adj deposition or low adj pressure adj "CVD" or "LPCVD") or spin adj on adj glass or "SOG" or tetra adj ethyl adj ortho adj silicate or tetraethyl adj orto adj silicate or tetraethyl adj orthosilicate or tetra adj ethylorthosilicate or tetraethylorthosilicate or "TEOS" )) and (insulat\$3 or dielectric) same thick\$4) and etch\$3 adj stop\$4 same ( ((nitride or "N.sub.?" ) same (plasma adj enhanced adj chemical adj vapor adj deposition or plasma adj enhanced adj "CVD" or plasma adj "ECVD" or "PECVD")) or (silicon or "Si") adj oxynitride or siliconoxynitride or silicon adj "ON" or "SiON" or (tantalum or "Ta") adj oxide or "Ta.sub.2" adj "O.sub.5" or (zinc or "Zn") adj oxide or "Zn" adj "O.sub.2" or "ZnO" or (zirconium or "Zr") adj oxide or "Zr" adj "O.sub.2" or (hafnium or "Hf") adj oxide or "HfO" or (aluminum or "Al") adj oxide or "Al.sub.2" adj "O.sub.3" )) and etch\$3 adj stop\$4 same thick\$4) and (conduct\$4 or metal\$8) same (aluminum or "Al" or copper or "Cu" or gold or "Au" or silver or "Ag" or chromium or "Cr")) and (conduct\$4 or metal\$8 or aluminum or "Al" or "Cu" or gold or "Au" or silver or "Ag" or chrome or chromium or "Cr" or thick\$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/19 08:19
-	1	"5723387".PN.	USPAT; US-PGPUB	2003/09/15 18:02
-	1	"5739579".PN.	USPAT; US-PGPUB	2003/09/15 18:03
-	1	"5753967".PN.	USPAT; US-PGPUB	2003/09/15 18:03
-	1	"5935762".PN.	USPAT; US-PGPUB	2003/09/15 18:07
-	1	"5989997".PN.	USPAT; US-PGPUB	2003/09/15 18:07
-	1	"6001414".PN.	USPAT; US-PGPUB	2003/09/15 18:08
-	1	"6001733".PN.	USPAT; US-PGPUB	2003/09/15 18:08
-	1	"6025226".PN.	USPAT; US-PGPUB	2003/09/15 18:09
-	1	"6027994".PN.	USPAT; US-PGPUB	2003/09/15 18:09
-	1	"6027994".PN.	USPAT; US-PGPUB	2003/09/15 18:10
-	1	"6027994".PN.	USPAT; US-PGPUB	2003/09/15 18:11
-	1	"6027994".PN.	USPAT; US-PGPUB	2003/09/15 18:11

-	1	"6028362".PN.	USPAT; US-PGPUB	2003/09/15 18:12
-	1	"6033977".PN.	USPAT; US-PGPUB	2003/09/15 18:12